

6367254 MOTOROLA SC (XSTRS/R F)

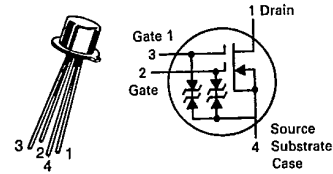
96D 82608 D
T-31-25

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V _{DS}	25	Vdc
Drain-Gate Voltage	V _{DG1} V _{DG2}	30 30	Vdc
Drain Current	I _D	50	mAdc
Gate Current	I _{G1} I _{G2}	±10 ±10	mAdc
Total Device Dissipation @ T _A = 25°C Derate above 25°C	P _D	360 2.4	mW mW/°C
Total Device Dissipation @ T _C = 25°C Derate above 25°C	P _D	1.2 8.0	Watt mW/°C
Lead Temperature	T _L	300	°C
Junction Temperature Range	T _J	-65 to +175	°C
Storage Channel Temperature Range	T _{stg}	-65 to +175	°C

**3N201
3N202
3N203**

**CASE 20-03, STYLE 9
TO-72 (TO-206AF)**



**DUAL-GATE MOSFET
VHF AMPLIFIER**

N-CHANNEL — DEPLETION

Refer to MPF201 for additional graphs.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Drain-Source Breakdown Voltage (I _D = 10 μAdc, V _S = 0, V _{G1S} = V _{G2S} = -5.0 Vdc)	V _{(BR)DSX}	25	—	—	Vdc
Gate 1-Source Breakdown Voltage(1) (I _{G1} = ±10 mAdc, V _{G2S} = V _{DS} = 0)	V _{(BR)G1SO}	±6.0	±12	±30	Vdc
Gate 2-Source Breakdown Voltage(1) (I _{G2} = ±10 mAdc, V _{G1S} = V _{DS} = 0)	V _{(BR)G2SO}	±6.0	±12	±30	Vdc
Gate 1 Leakage Current (V _{G1S} = ±5.0 Vdc, V _{G2S} = V _{DS} = 0) (V _{G1S} = -5.0 Vdc, V _{G2S} = V _{DS} = 0, T _A = 150°C)	I _{G1SS}	—	±.040	±10	nAdc μAdc
Gate 2 Leakage Current (V _{G2S} = ±5.0 Vdc, V _{G1S} = V _{DS} = 0) (V _{G2S} = -5.0 Vdc, V _{G1S} = V _{DS} = 0, T _A = 150°C)	I _{G2SS}	—	±.050	±10	nAdc μAdc
Gate 1 to Source Cutoff Voltage (V _{DS} = 15 Vdc, V _{G2S} = 4.0 Vdc, I _D = 20 μAdc)	V _{G1S(off)}	-0.5	-1.5	-5.0	Vdc
Gate 2 to Source Cutoff Voltage (V _{DS} = 15 Vdc, V _{G1S} = 0, I _D = 20 μAdc)	V _{G2S(off)}	-0.2	-1.4	-5.0	Vdc
ON CHARACTERISTICS					
Zero-Gate-Voltage Drain Current(2) (V _{DS} = 15 Vdc, V _{G1S} = 0, V _{G2S} = 4.0 Vdc)	I _{DSS}	6.0 3.0	13 11	30 15	mAdc
SMALL-SIGNAL CHARACTERISTICS					
Forward Transfer Admittance(3) (V _{DS} = 15 Vdc, V _{G2S} = 4.0 Vdc, V _{G1S} = 0, f = 1.0 kHz)	Y _{fs}	8.0 7.0	12.8 12.5	20 15	mmhos
Input Capacitance (V _{DS} = 15 Vdc, V _{G2S} = 4.0 Vdc, I _D = I _{DSS} , f = 1.0 MHz)	C _{iss}	—	3.3	—	pF
Reverse Transfer Capacitance (V _{DS} = 15 Vdc, V _{G2S} = 4.0 Vdc, I _D = 10 mAdc, f = 1.0 MHz)	C _{rss}	0.005	0.014	0.03	pF
Output Capacitance (V _{DS} = 15 Vdc, V _{G2S} = 4.0 Vdc, I _D = I _{DSS} , f = 1.0 MHz)	C _{oss}	—	1.7	—	pF
FUNCTIONAL CHARACTERISTICS					
Noise Figure (V _{DD} = 18 Vdc, V _{GG} = 7.0 Vdc, f = 200 MHz) (Figure 1) (V _{DD} = 18 Vdc, V _{GG} = 6.0 Vdc, f = 45 MHz) (Figure 3)	NF	—	1.8 5.3	4.5 6.0	dB

MOTOROLA SMALL-SIGNAL SEMICONDUCTORS

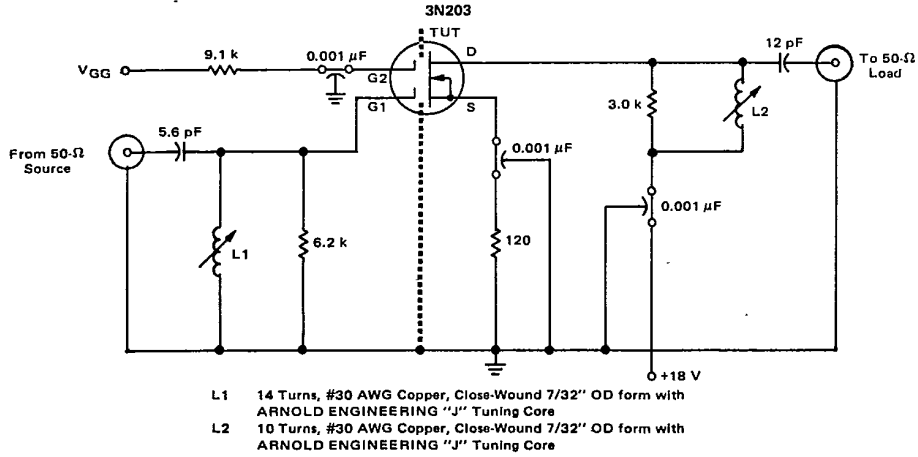
6367254 MOTOROLA SC (XSTRS/R F)

96D 82610 D

3N201, 3N202, 3N203

T-31-25

FIGURE 3 - 45-MHz TEST CIRCUIT SCHEMATIC



6

TYPICAL CHARACTERISTICS

FIGURE 4 - DRAIN CURRENT versus DRAIN to SOURCE VOLTAGE

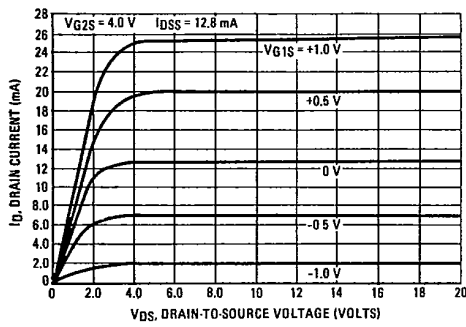


FIGURE 5 - DRAIN CURRENT versus GATE-ONE to SOURCE VOLTAGE

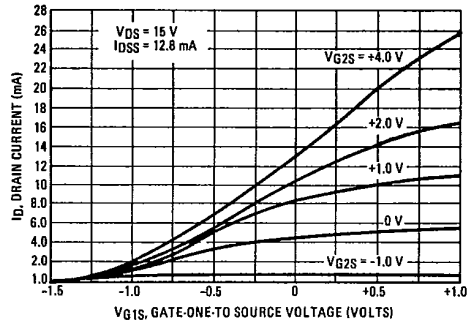


FIGURE 6 - SMALL-SIGNAL COMMON-SOURCE GATE-ONE FORWARD TRANSFER ADMITTANCE versus DRAIN CURRENT

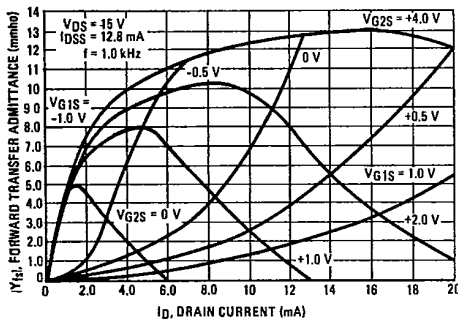
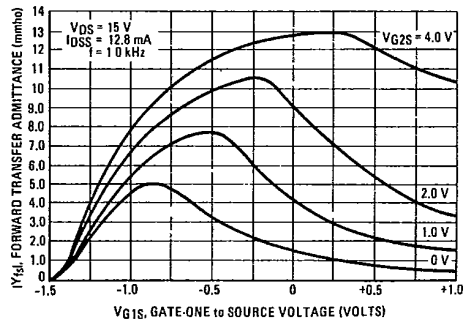


FIGURE 7 - SMALL-SIGNAL COMMON-SOURCE GATE-ONE FORWARD TRANSFER ADMITTANCE versus GATE-ONE to SOURCE VOLTAGE



6367254 MOTOROLA SC (XSTRS/R F)

96D 82611 D

3N201, 3N202, 3N203

T-31-25

FIGURE 8 - SMALL-SIGNAL COMMON-SOURCE GATE-ONE FORWARD TRANSFER ADMITTANCE versus GATE-TWO to SOURCE VOLTAGE

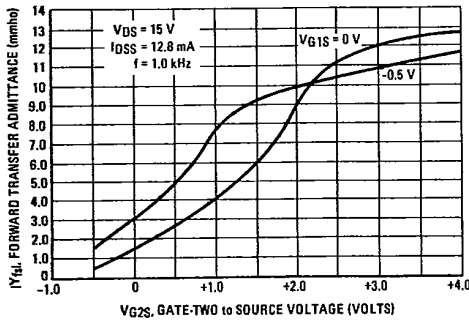
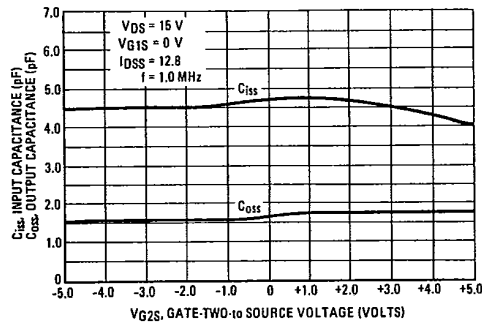


FIGURE 9 - SMALL-SIGNAL COMMON-SOURCE GATE-ONE INPUT AND OUTPUT CAPACITANCE versus GATE-TWO to SOURCE VOLTAGE



TYPICAL CHARACTERISTICS

FIGURE 10 - COMMON-SOURCE POWER GAIN AND SPOT NOISE FIGURE versus DRAIN CURRENT

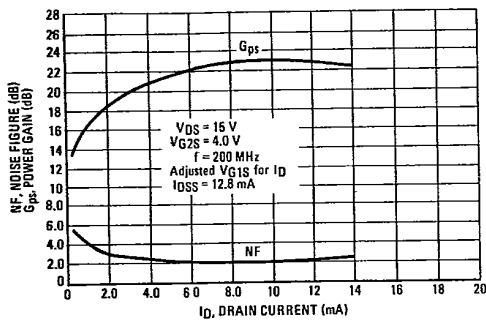


FIGURE 11 - COMMON-SOURCE POWER GAIN AND SPOT NOISE FIGURE versus GAIN CONTROL GATE-SUPPLY VOLTAGE - 3N201

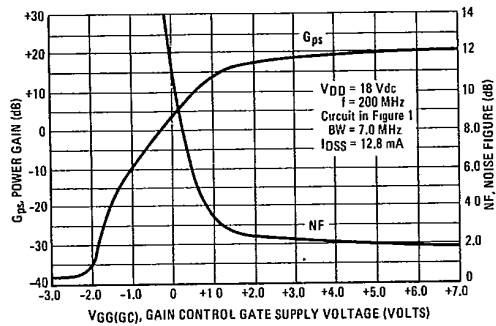


FIGURE 12 - COMMON-SOURCE POWER GAIN versus DRAIN SUPPLY CURRENT - 3N201

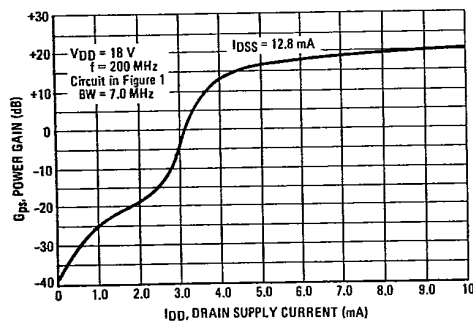
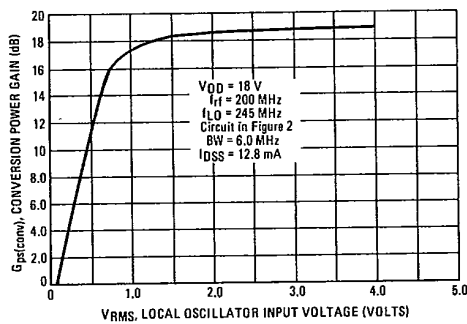


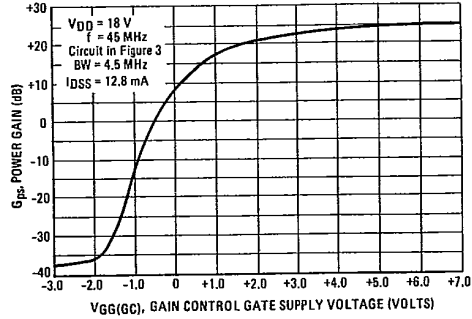
FIGURE 13 - SMALL-SIGNAL COMMON-SOURCE CONVERSION POWER GAIN versus LOCAL OSCILLATOR INPUT VOLTAGE - 3N202



6367254 MOTOROLA SC (XSTRS/R F)
 3N201, 3N202, 3N203

96D 82612 D
 T-31-25

FIGURE 14 - SMALL-SIGNAL COMMON SOURCE
 INSERTION POWER GAIN versus GAIN CONTROL
 GATE-SUPPLY VOLTAGE - 3N203



6

TYPICAL CHARACTERISTICS

FIGURE 15 - SMALL-SIGNAL GATE ONE FORWARD
 TRANSFER ADMITTANCE versus FREQUENCY

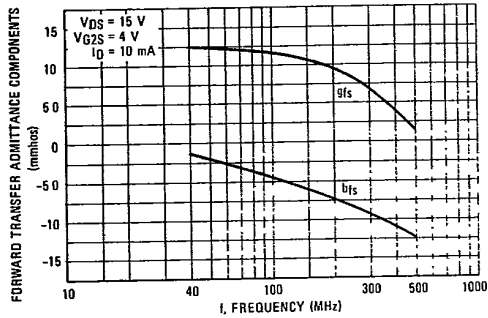


FIGURE 16 - SMALL-SIGNAL GATE ONE INPUT
 ADMITTANCE versus FREQUENCY

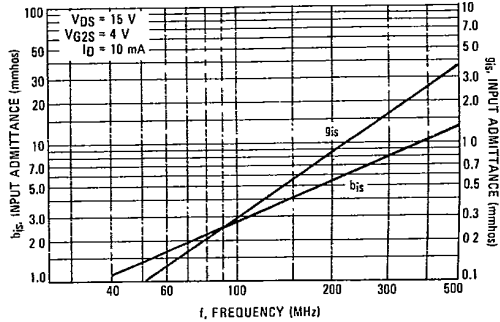
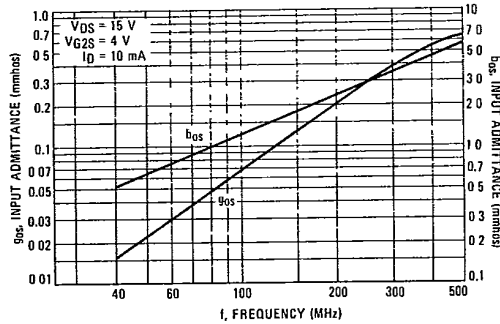


FIGURE 17 - SMALL-SIGNAL GATE ONE OUTPUT
 ADMITTANCE versus FREQUENCY



MOTOROLA SMALL-SIGNAL SEMICONDUCTORS